

DESCRIPTION

The MX30P15 uses advanced trench technology to provide excellent $R_{DS(ON)}$. This device is suitable for use as a load switch or in PWM applications.

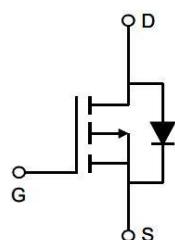
GENERAL FEATURES

- $V_{DS}=-30V$, $I_D=-15A$
- $R_{DS(ON)}(\text{Typ.})=11.5\text{m}\Omega$ @ $V_{GS}=-4.5V$
- $R_{DS(ON)}(\text{Typ.})=8.5\text{m}\Omega$ @ $V_{GS}=-10V$
- High Power and current handing capability
- Lead free product is acquired
- Surface Mount Package

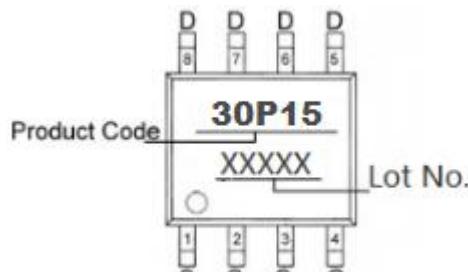
APPLICATION

- PWM applications
- Load switch
- Power management

PINOUT



Schematic diagram



Marking and pin Assignment



SOP-8 top view

ORDERING INFORMATION

Part Number	Storage Temperature	Package	Devices Per Reel
MX30P15	-55°C to 150°C	SOP-8	-

ABSOLUTE MAXIMUM RATINGS($T_A=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	-30	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	-15	A
Pulsed Drain Current ^(Note1)	I_{DM}	-80	A
Maximum Power Dissipation	P_D	3.1	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	°C

THERMAL RESISTANCE

Thermal Resistance, Junction-to-Ambient ^(Note2)	$R_{\theta JA}$	40	°C/W
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Note 1. Repetitive Rating: Pulse width limited by maximum junction temperature.

Note 2. Surface Mounted on FR4 Board, $t \leq 10$ sec.


ELECTRICAL CHARACTERISTICS($T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
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Off Characteristics

Drain-Source Breakdown Voltage	BV_{DSS}	$V_{\text{GS}}=0\text{V}, I_{\text{D}}=-250\mu\text{A}$	-30	-33	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{\text{DS}}=-30\text{V}, V_{\text{GS}}=0\text{V}$	-	-	-1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{\text{GS}}=\pm 20\text{V}, V_{\text{DS}}=0\text{V}$	-	-	± 100	nA

On Characteristics^(Note 3)

Gate Threshold Voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{DS}}=V_{\text{GS}}, I_{\text{D}}=-250\mu\text{A}$	-1.0	-1.5	-2.2	V
Drain-Source On-State Resistance	$R_{\text{DS}(\text{ON})}$	$V_{\text{GS}}=-4.5\text{V}, I_{\text{D}}=-6\text{A}$	-	11.5	15	$\text{m}\Omega$
		$V_{\text{GS}}=-10\text{V}, I_{\text{D}}=-15\text{A}$	-	8.5	12	$\text{m}\Omega$
Forward Transconductance	g_{FS}	$V_{\text{DS}}=-5\text{V}, I_{\text{D}}=-15\text{A}$	30	-	-	S

Dynamic Characteristics^(Note 4)

Input Capacitance	C_{iss}	$V_{\text{DS}}=-15\text{V}, V_{\text{GS}}=0\text{V}, F=1.0\text{MHz}$	-	2900	-	pF
Output Capacitance	C_{oss}		-	410	-	pF
Reverse Transfer Capacitance	C_{rss}		-	280	-	pF

Switching Characteristics^(Note 4)

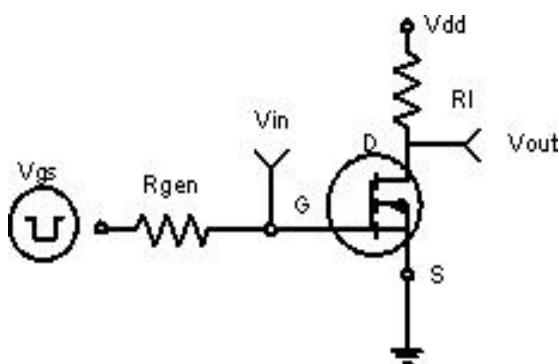
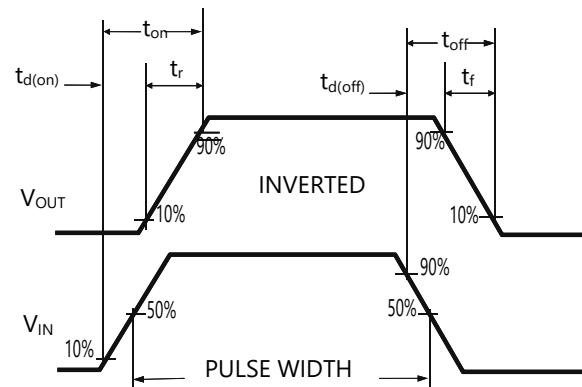
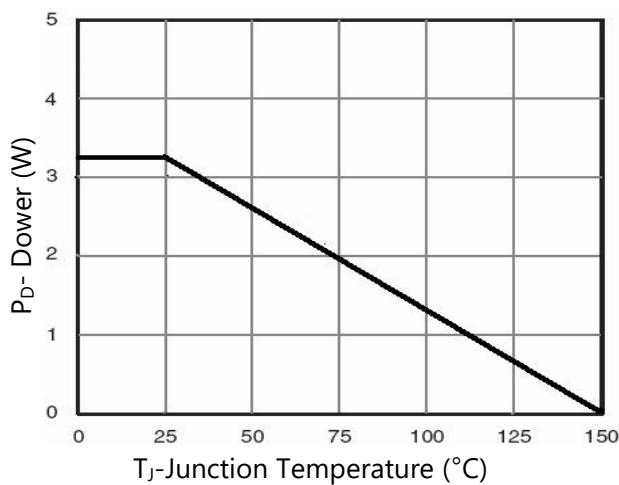
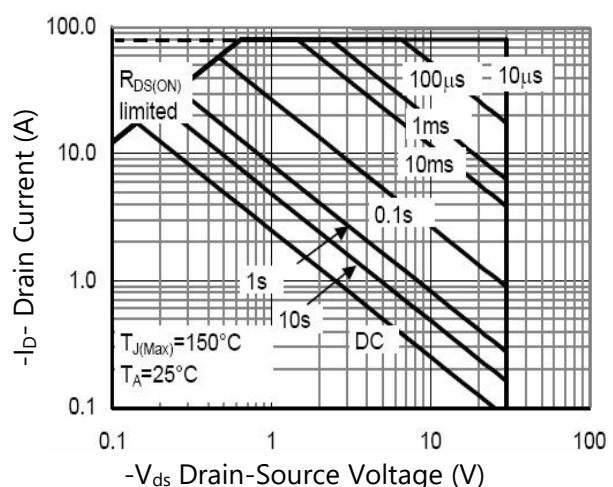
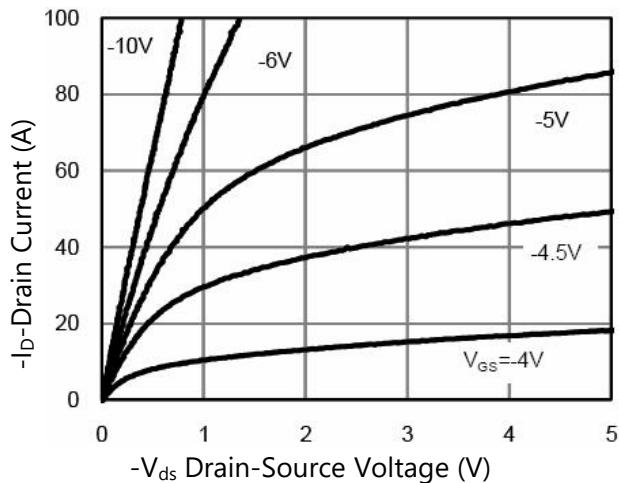
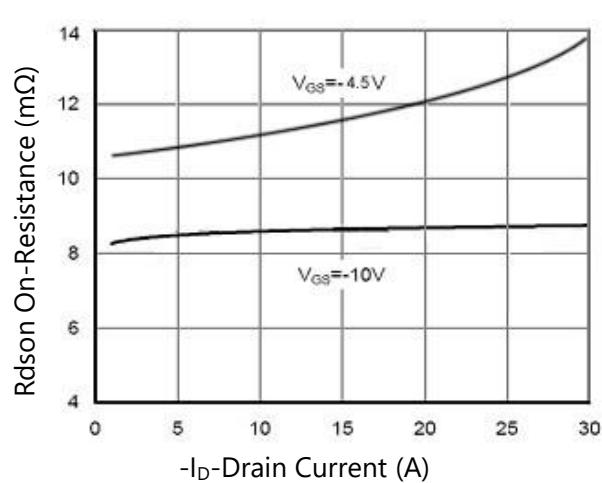
Turn-on Delay Time	$t_{\text{d}(\text{on})}$	$V_{\text{DD}}=-15\text{V}, I_{\text{D}}=-10\text{A}, V_{\text{GS}}=-10\text{V}, R_{\text{GEN}}=3\Omega$	-	15	-	nS
Turn-on Rise Time	t_{r}		-	11	-	nS
Turn-Off Delay Time	$t_{\text{d}(\text{off})}$		-	44	-	nS
Turn-Off Fall Time	t_{f}		-	21	-	nS
Total Gate Charge	Q_{g}	$V_{\text{DS}}=-15\text{V}, I_{\text{D}}=-10\text{A}, V_{\text{GS}}=-10\text{V}$	-	48	-	nC
Gate-Source Charge	Q_{gs}		-	12	-	nC
Gate-Drain Charge	Q_{gd}		-	14	-	nC

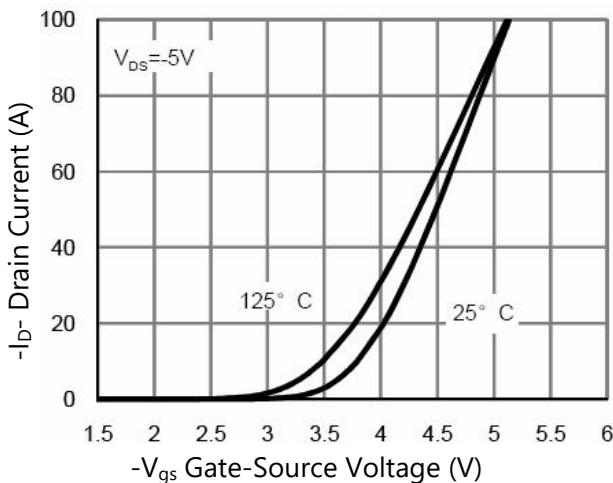
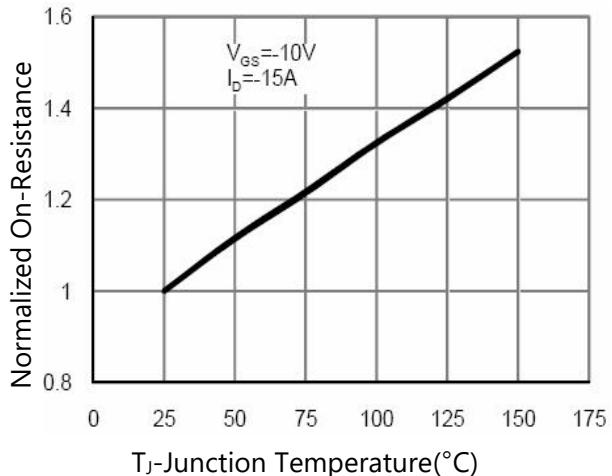
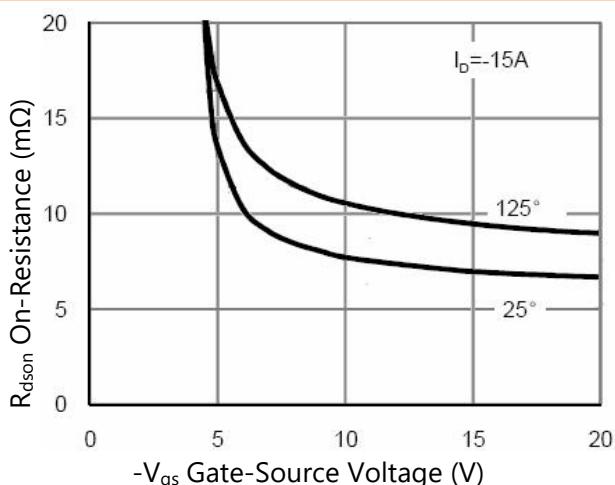
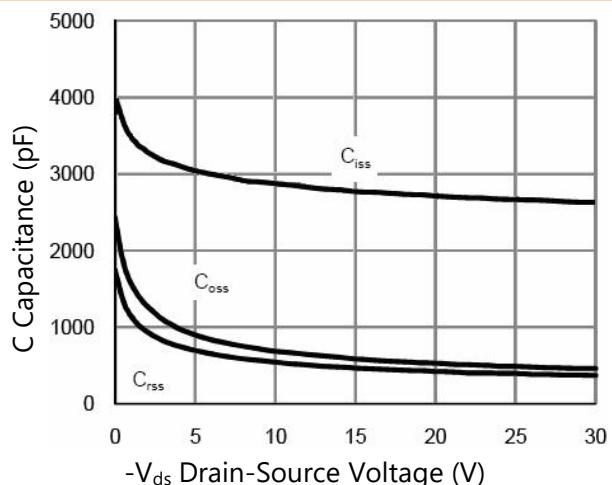
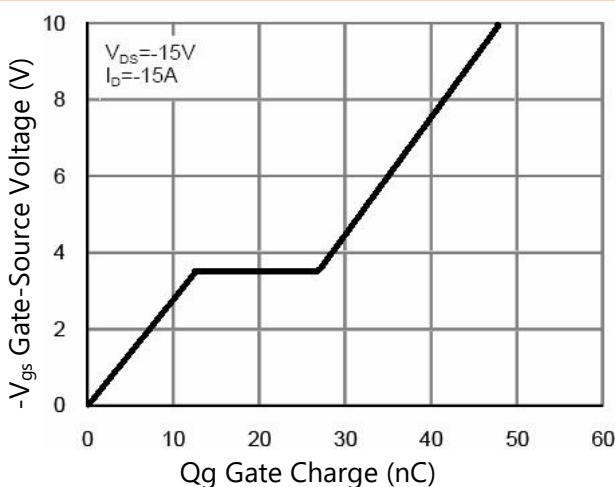
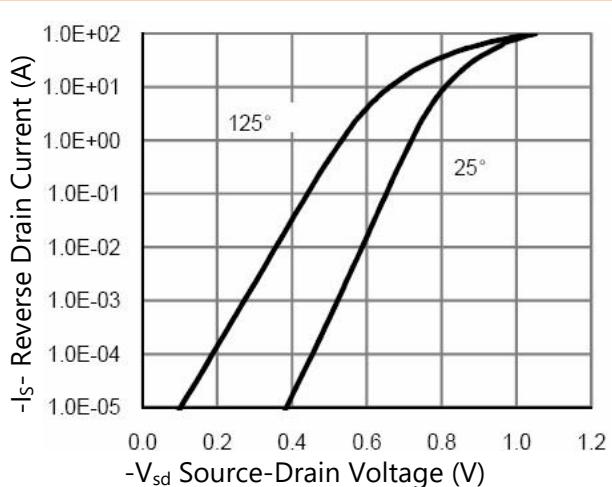
Drain-Source Diode Characteristics

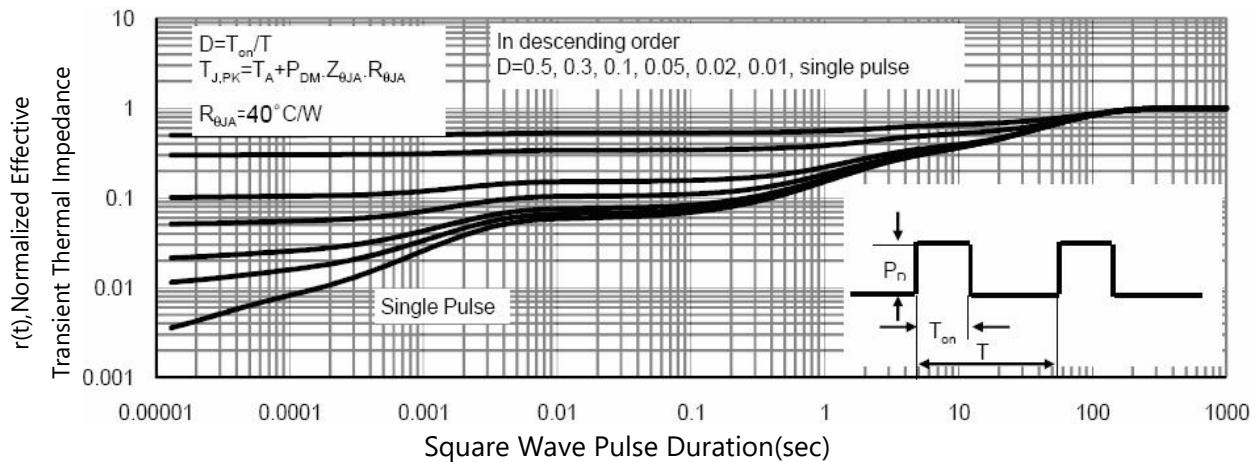
Diode Forward Voltage ^(Note 3)	V_{SD}	$V_{\text{GS}}=0\text{V}, I_{\text{S}}=-2\text{A}$	-	-	-1.2	V
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Note 3. Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2\%$.

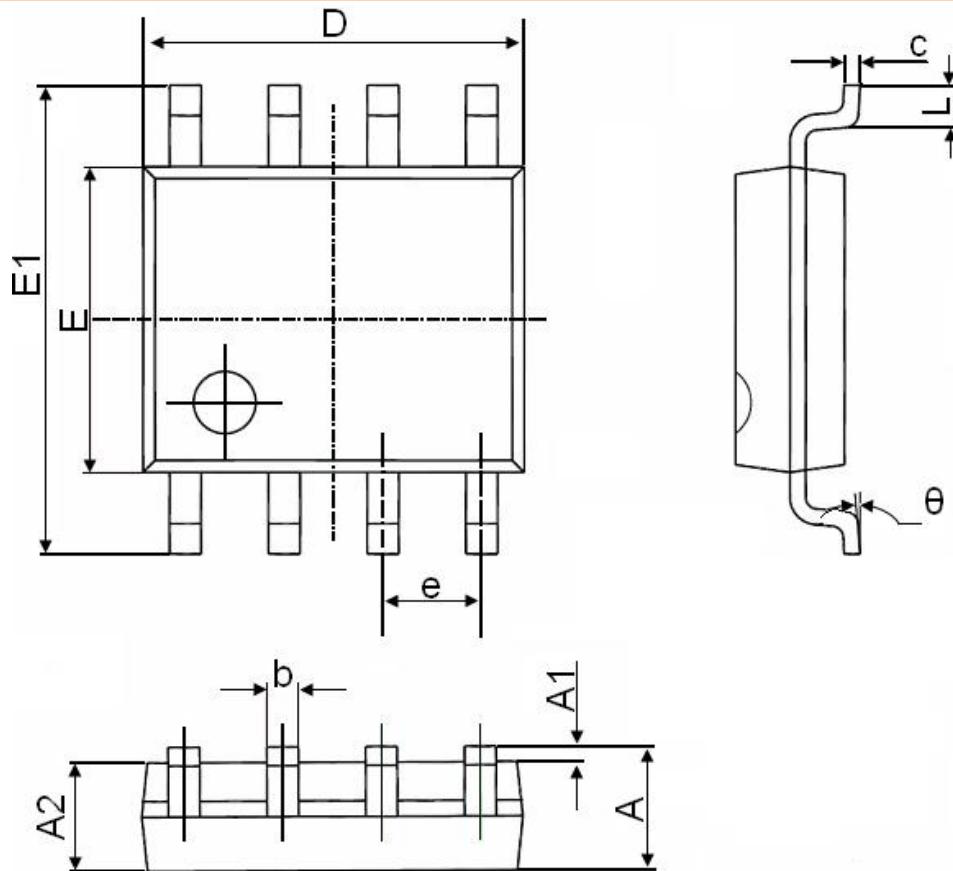
Note 4. Guaranteed by design, not subject to product.


TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS
Figure 1. Switching Test Circuit

Figure 2. Switching Waveform

Figure 3. Power Dissipation

Figure 4. Safe Operation Area

Figure 5. Output Characteristics

Figure 6. Rdson vs Drain Current



TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS
Figure 7. Transfer Characteristics

Figure 8. R_{DSON} vs Junction Temperature

Figure 9. R_{DSON} vs V_{GS}

Figure 10. Capacitance vs V_{DS}

Figure 11. Gate Charge

Figure 12. Source- Drain Diode Forward



TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS
Figure 13. Normalized Maximum Transient Thermal Impedance


PACKAGE INFORMATION

SOP-8


Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270(BSC)		0.050(BSC)	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°